ABSTRACT

A non-volatile memory device may include a channel structure including a first stacking structure, a second stacking structure, a first channel structure penetrating the first stacking structure, and a second channel structure penetrating the second stacking structure. The second channel structure includes a first portion having a width that decreases or is maintained as the first portion extends toward the substrate, and a second portion having a width that increases as the second portion extends toward the substrate.

FIG. 2